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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	55296
Number of I/O	151
Number of Gates	400000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p400-2pq208

Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3 device provides the best available security for programmable logic designs.

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based ProASIC3 FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based ProASIC3 devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based ProASIC3 devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs that are used for these purposes in a system. In addition, glitches and brownouts in system power will not corrupt the ProASIC3 device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based ProASIC3 devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of ProASIC3 flash-based FPGAs. Once it is programmed, the flash cell configuration element of ProASIC3 FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Low Power

Flash-based ProASIC3 devices exhibit power characteristics similar to an ASIC, making them an ideal choice for power-sensitive applications. ProASIC3 devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

ProASIC3 devices also have low dynamic power consumption to further maximize power savings.

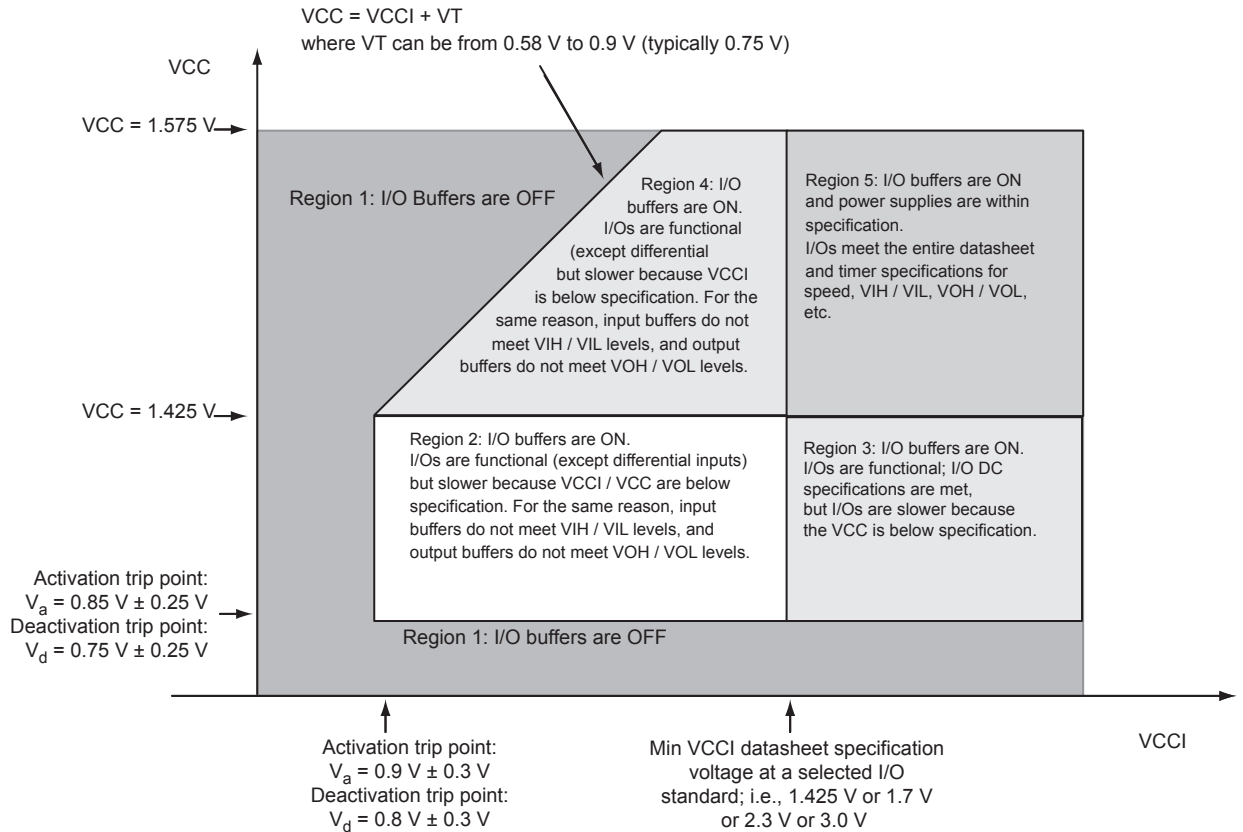


Figure 2-2 • I/O State as a Function of $VCCI$ and VCC Voltage Levels

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja} . The thermal characteristics for θ_{ja} are shown for two air flow rates.

Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices

Parameter	Definition	Device Specific Static Power (mW)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PDC1	Array static power in Active mode	See Table 2-7 on page 2-7.							
PDC2	I/O input pin static power (standard-dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PDC3	I/O output pin static power (standard-dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PDC4	Static PLL contribution	2.55 mW							
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-7 on page 2-7.							

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-16 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-17 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-17 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = P_{DC1} + N_{INPUTS} * P_{DC2} + N_{OUTPUTS} * P_{DC3}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

Table 2-45 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-46 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
4 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
6 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns
8 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-61 • 2.5 V LVCMOS Low Slew

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$

Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	11.40	0.04	1.31	0.43	11.22	11.40	2.68	2.20	13.45	13.63	ns
	–1	0.51	9.69	0.04	1.11	0.36	9.54	9.69	2.28	1.88	11.44	11.60	ns
	–2	0.45	8.51	0.03	0.98	0.32	8.38	8.51	2.00	1.65	10.05	10.18	ns
6 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
8 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
12 mA	Std.	0.60	6.18	0.04	1.31	0.43	6.29	5.92	3.30	3.32	8.53	8.15	ns
	–1	0.51	5.26	0.04	1.11	0.36	5.35	5.03	2.81	2.83	7.26	6.94	ns
	–2	0.45	4.61	0.03	0.98	0.32	4.70	4.42	2.47	2.48	6.37	6.09	ns
16 mA	Std.	0.60	5.76	0.04	1.31	0.43	5.87	5.53	3.36	3.44	8.11	7.76	ns
	–1	0.51	4.90	0.04	1.11	0.36	4.99	4.70	2.86	2.92	6.90	6.60	ns
	–2	0.45	4.30	0.03	0.98	0.32	4.38	4.13	2.51	2.57	6.05	5.80	ns
24 mA	Std.	0.60	5.51	0.04	1.31	0.43	5.50	5.51	3.43	3.87	7.74	7.74	ns
	–1	0.51	4.68	0.04	1.11	0.36	4.68	4.68	2.92	3.29	6.58	6.59	ns
	–2	0.45	4.11	0.03	0.98	0.32	4.11	4.11	2.56	2.89	5.78	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-62 • 2.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.28	0.04	1.30	0.43	7.41	8.28	2.25	2.07	9.64	10.51	ns
	–1	0.56	7.04	0.04	1.10	0.36	6.30	7.04	1.92	1.76	8.20	8.94	ns
	–2	0.49	6.18	0.03	0.97	0.32	5.53	6.18	1.68	1.55	7.20	7.85	ns
6 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
8 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
12 mA	Std.	0.66	3.21	0.04	1.30	0.43	3.27	3.14	2.82	3.11	5.50	5.38	ns
	–1	0.56	2.73	0.04	1.10	0.36	2.78	2.67	2.40	2.65	4.68	4.57	ns
	–2	0.49	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-63 • 2.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	10.84	0.04	1.30	0.43	10.64	10.84	2.26	1.99	12.87	13.08	ns
	–1	0.56	9.22	0.04	1.10	0.36	9.05	9.22	1.92	1.69	10.95	11.12	ns
	–2	0.49	8.10	0.03	0.97	0.32	7.94	8.10	1.68	1.49	9.61	9.77	ns
6 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
8 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
12 mA	Std.	0.66	5.63	0.04	1.30	0.43	5.73	5.51	2.83	3.01	7.97	7.74	ns
	–1	0.56	4.79	0.04	1.10	0.36	4.88	4.68	2.41	2.56	6.78	6.59	ns
	–2	0.49	4.20	0.03	0.97	0.32	4.28	4.11	2.11	2.25	5.95	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-66 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	11	9	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	22	17	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	44	35	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	51	45	10	10
12 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	12	12	74	91	10	10
16 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	16	16	74	91	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-67 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	2	2	11	9	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	4	4	22	17	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	6	6	44	35	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	8	8	44	35	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-73 • 1.8 V LVC MOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	–1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	–2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	–1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	–2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-74 • 1.8 V LVC MOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
 Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	–1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	–2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	–1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	–2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Input Register

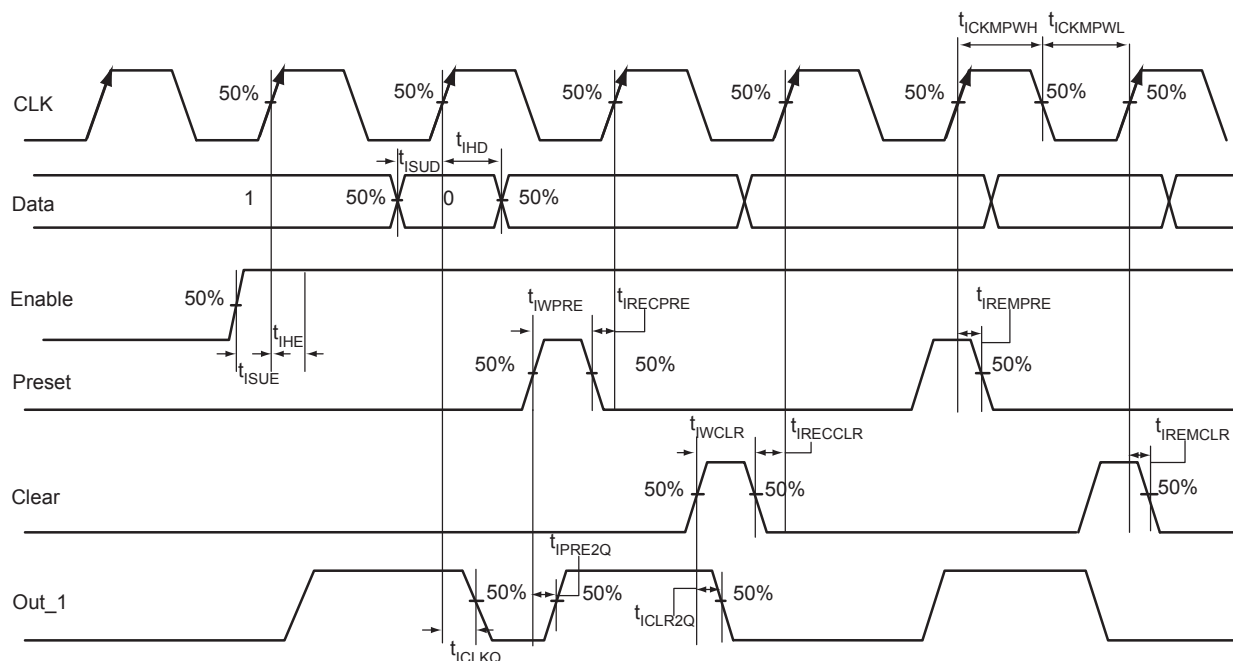


Figure 2-17 • Input Register Timing Diagram

Timing Characteristics

Table 2-98 • Input Data Register Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.24	0.27	0.32	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.26	0.30	0.35	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.37	0.42	0.50	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IEMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IEMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{ICKMPWH}	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.41	0.48	ns
t_{ICKMPWL}	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

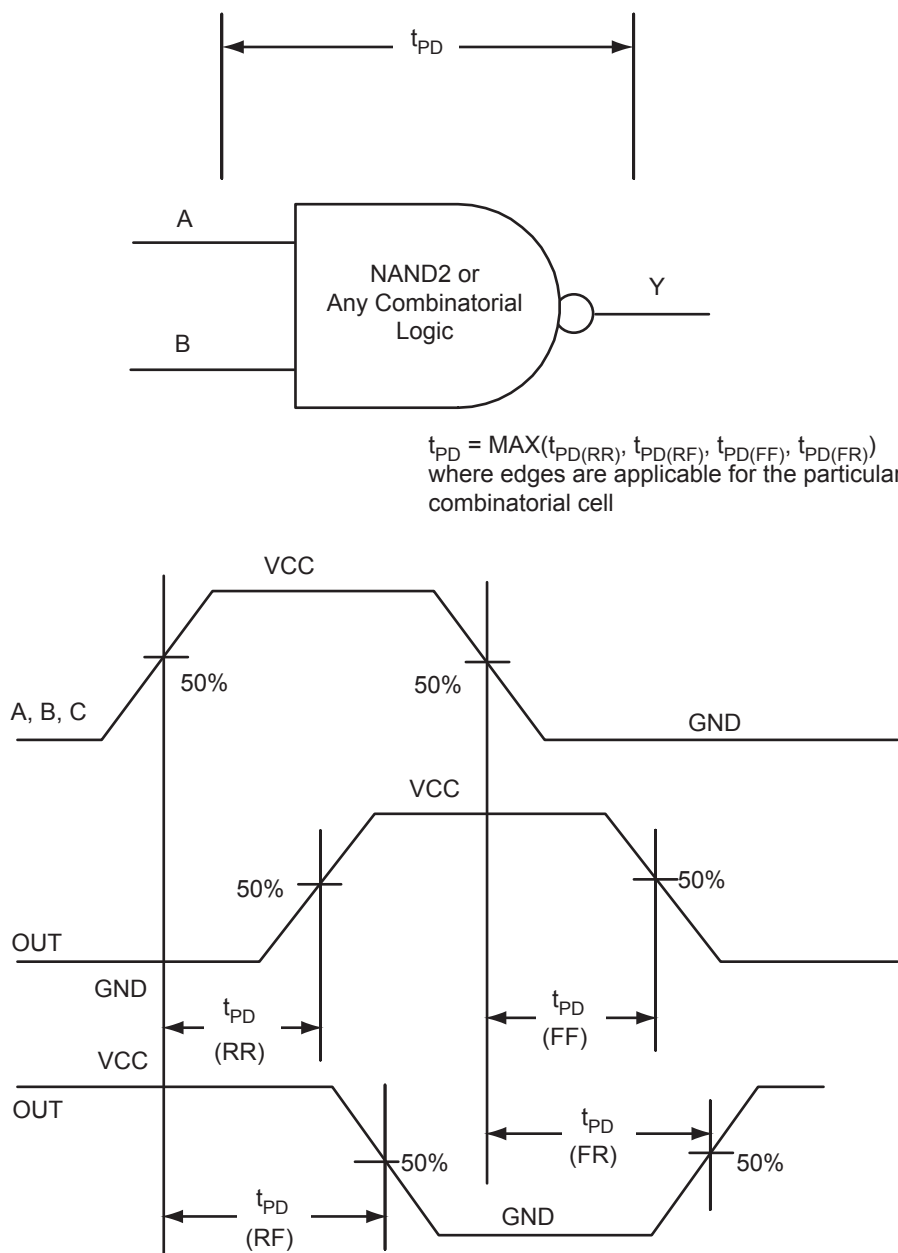


Figure 2-25 • Timing Model and Waveforms

Table 2-109 • A3P060 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.71	0.93	0.81	1.05	0.95	1.24	ns
t_{RCKH}	Input High Delay for Global Clock	0.70	0.96	0.80	1.09	0.94	1.28	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-110 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.77	0.99	0.87	1.12	1.03	1.32	ns
t_{RCKH}	Input High Delay for Global Clock	0.76	1.02	0.87	1.16	1.02	1.37	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

3 – Pin Descriptions

Supply Pins

GND **Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ **Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC **Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx **I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. In general, unused I/O banks should have their corresponding VCCIX pins tied to GND. If an output pad is terminated to ground through any resistor and if the corresponding VCCIX is left floating, then the leakage current to ground is ~ 0uA. However, if an output pad is terminated to ground through any resistor and the corresponding VCCIX grounded, then the leakage current to ground is ~ 3 uA. For unused banks the aforementioned behavior is to be taken into account while deciding if it's better to float VCCIX of unused bank or tie it to GND.

VMVx **I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F **PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the [ProASIC3 FPGA Fabric User's Guide](#) for a complete board solution for the PLL analog power supply and ground.

There is one VCCPLF pin on ProASIC3 devices.

VCOMPLA/B/C/D/E/F **PLL Ground**

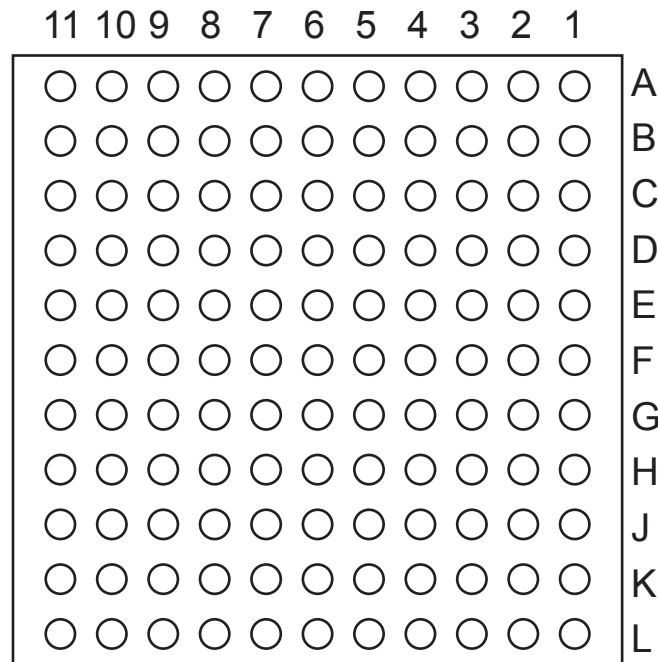
Ground to analog PLL power supplies. When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on ProASIC3 devices.

QN48	
Pin Number	A3P030 Function
1	IO82RSB1
2	GEC0/IO73RSB1
3	GEA0/IO72RSB1
4	GEB0/IO71RSB1
5	GND
6	VCCIB1
7	IO68RSB1
8	IO67RSB1
9	IO66RSB1
10	IO65RSB1
11	IO64RSB1
12	IO62RSB1
13	IO61RSB1
14	IO60RSB1
15	IO57RSB1
16	IO55RSB1
17	IO53RSB1
18	VCC
19	VCCIB1
20	IO46RSB1
21	IO42RSB1
22	TCK
23	TDI
24	TMS
25	VPUMP
26	TDO
27	TRST
28	VJTAG
29	IO38RSB0
30	GDB0/IO34RSB0
31	GDA0/IO33RSB0
32	GDC0/IO32RSB0
33	VCCIB0
34	GND
35	VCC
36	IO25RSB0

QN48	
Pin Number	A3P030 Function
37	IO24RSB0
38	IO22RSB0
39	IO20RSB0
40	IO18RSB0
41	IO16RSB0
42	IO14RSB0
43	IO10RSB0
44	IO08RSB0
45	IO06RSB0
46	IO04RSB0
47	IO02RSB0
48	IO00RSB0

CS121 – Bottom View



Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

VQ100		VQ100		VQ100	
Pin Number	A3P030 Function	Pin Number	A3P030 Function	Pin Number	A3P030 Function
1	GND	37	VCC	73	IO27RSB0
2	IO82RSB1	38	GND	74	IO26RSB0
3	IO81RSB1	39	VCCIB1	75	IO25RSB0
4	IO80RSB1	40	IO49RSB1	76	IO24RSB0
5	IO79RSB1	41	IO47RSB1	77	IO23RSB0
6	IO78RSB1	42	IO46RSB1	78	IO22RSB0
7	IO77RSB1	43	IO45RSB1	79	IO21RSB0
8	IO76RSB1	44	IO44RSB1	80	IO20RSB0
9	GND	45	IO43RSB1	81	IO19RSB0
10	IO75RSB1	46	IO42RSB1	82	IO18RSB0
11	IO74RSB1	47	TCK	83	IO17RSB0
12	GEC0/IO73RSB1	48	TDI	84	IO16RSB0
13	GEA0/IO72RSB1	49	TMS	85	IO15RSB0
14	GEB0/IO71RSB1	50	NC	86	IO14RSB0
15	IO70RSB1	51	GND	87	VCCIB0
16	IO69RSB1	52	VPUMP	88	GND
17	VCC	53	NC	89	VCC
18	VCCIB1	54	TDO	90	IO12RSB0
19	IO68RSB1	55	TRST	91	IO10RSB0
20	IO67RSB1	56	VJTAG	92	IO08RSB0
21	IO66RSB1	57	IO41RSB0	93	IO07RSB0
22	IO65RSB1	58	IO40RSB0	94	IO06RSB0
23	IO64RSB1	59	IO39RSB0	95	IO05RSB0
24	IO63RSB1	60	IO38RSB0	96	IO04RSB0
25	IO62RSB1	61	IO37RSB0	97	IO03RSB0
26	IO61RSB1	62	IO36RSB0	98	IO02RSB0
27	IO60RSB1	63	GDB0/IO34RSB0	99	IO01RSB0
28	IO59RSB1	64	GDA0/IO33RSB0	100	IO00RSB0
29	IO58RSB1	65	GDC0/IO32RSB0		
30	IO57RSB1	66	VCCIB0		
31	IO56RSB1	67	GND		
32	IO55RSB1	68	VCC		
33	IO54RSB1	69	IO31RSB0		
34	IO53RSB1	70	IO30RSB0		
35	IO52RSB1	71	IO29RSB0		
36	IO51RSB1	72	IO28RSB0		

PQ208	
Pin Number	A3P1000 Function
109	TRST
110	VJTAG
111	GDA0/IO113NDB1
112	GDA1/IO113PDB1
113	GDB0/IO112NDB1
114	GDB1/IO112PDB1
115	GDC0/IO111NDB1
116	GDC1/IO111PDB1
117	IO109NDB1
118	IO109PDB1
119	IO106NDB1
120	IO106PDB1
121	IO104PSB1
122	GND
123	VCCIB1
124	IO99NDB1
125	IO99PDB1
126	NC
127	IO96NDB1
128	GCC2/IO96PDB1
129	GCB2/IO95PSB1
130	GND
131	GCA2/IO94PSB1
132	GCA1/IO93PDB1
133	GCA0/IO93NDB1
134	GCB0/IO92NDB1
135	GCB1/IO92PDB1
136	GCC0/IO91NDB1
137	GCC1/IO91PDB1
138	IO88NDB1
139	IO88PDB1
140	VCCIB1
141	GND
142	VCC
143	IO86PSB1
144	IO84NDB1

PQ208	
Pin Number	A3P1000 Function
145	IO84PDB1
146	IO82NDB1
147	IO82PDB1
148	IO80NDB1
149	GBC2/IO80PDB1
150	IO79NDB1
151	GBB2/IO79PDB1
152	IO78NDB1
153	GBA2/IO78PDB1
154	VMV1
155	GNDQ
156	GND
157	VMV0
158	GBA1/IO77RSB0
159	GBA0/IO76RSB0
160	GBB1/IO75RSB0
161	GBB0/IO74RSB0
162	GND
163	GBC1/IO73RSB0
164	GBC0/IO72RSB0
165	IO70RSB0
166	IO67RSB0
167	IO63RSB0
168	IO60RSB0
169	IO57RSB0
170	VCCIB0
171	VCC
172	IO54RSB0
173	IO51RSB0
174	IO48RSB0
175	IO45RSB0
176	IO42RSB0
177	IO40RSB0
178	GND
179	IO38RSB0
180	IO35RSB0

PQ208	
Pin Number	A3P1000 Function
181	IO33RSB0
182	IO31RSB0
183	IO29RSB0
184	IO27RSB0
185	IO25RSB0
186	VCCIB0
187	VCC
188	IO22RSB0
189	IO20RSB0
190	IO18RSB0
191	IO16RSB0
192	IO15RSB0
193	IO14RSB0
194	IO13RSB0
195	GND
196	IO12RSB0
197	IO11RSB0
198	IO10RSB0
199	IO09RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

FG144	
Pin Number	A3P060 Function
K1	GEB0/IO74RSB1
K2	GEA1/IO73RSB1
K3	GEA0/IO72RSB1
K4	GEA2/IO71RSB1
K5	IO65RSB1
K6	IO64RSB1
K7	GND
K8	IO57RSB1
K9	GDC2/IO56RSB1
K10	GND
K11	GDA0/IO50RSB0
K12	GDB0/IO48RSB0
L1	GND
L2	VMV1
L3	GEB2/IO70RSB1
L4	IO67RSB1
L5	VCCIB1
L6	IO62RSB1
L7	IO59RSB1
L8	IO58RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO69RSB1
M3	IO68RSB1
M4	IO66RSB1
M5	IO63RSB1
M6	IO61RSB1
M7	IO60RSB1
M8	NC
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	A3P600 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO10RSB0
A6	GND
A7	IO34RSB0
A8	VCC
A9	IO50RSB0
A10	GBA0/IO58RSB0
A11	GBA1/IO59RSB0
A12	GNDQ
B1	GAB2/IO173PDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO13RSB0
B6	IO19RSB0
B7	IO31RSB0
B8	IO39RSB0
B9	GBB0/IO56RSB0
B10	GBB1/IO57RSB0
B11	GND
B12	VMV1
C1	IO173NDB3
C2	GFA2/IO161PPB3
C3	GAC2/IO172PDB3
C4	VCC
C5	IO16RSB0
C6	IO25RSB0
C7	IO28RSB0
C8	IO42RSB0
C9	IO45RSB0
C10	GBA2/IO60PDB1
C11	IO60NDB1
C12	GBC2/IO62PPB1

FG144	
Pin Number	A3P600 Function
D1	IO169PDB3
D2	IO169NDB3
D3	IO172NDB3
D4	GAA2/IO174PPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO54RSB0
D8	GBC1/IO55RSB0
D9	GBB2/IO61PDB1
D10	IO61NDB1
D11	IO62NPB1
D12	GCB1/IO70PPB1
E1	VCC
E2	GFC0/IO164NDB3
E3	GFC1/IO164PDB3
E4	VCCIB3
E5	IO174NPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO69PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO71NDB1
E12	IO72NDB1
F1	GFB0/IO163NPB3
F2	VCOMPLF
F3	GFB1/IO163PPB3
F4	IO161NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO69NDB1
F9	GCB0/IO70NPB1
F10	GND
F11	GCA1/IO71PDB1
F12	GCA2/IO72PDB1

FG144	
Pin Number	A3P600 Function
G1	GFA1/IO162PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO162NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO86PPB1
G9	IO74NDB1
G10	GCC2/IO74PDB1
G11	IO73NDB1
G12	GCB2/IO73PDB1
H1	VCC
H2	GFB2/IO160PDB3
H3	GFC2/IO159PSB3
H4	GEC1/IO146PDB3
H5	VCC
H6	IO80PDB1
H7	IO80NDB1
H8	GDB2/IO90RSB2
H9	GDC0/IO86NPB1
H10	VCCIB1
H11	IO84PSB1
H12	VCC
J1	GEB1/IO145PDB3
J2	IO160NDB3
J3	VCCIB3
J4	GEC0/IO146NDB3
J5	IO129RSB2
J6	IO131RSB2
J7	VCC
J8	TCK
J9	GDA2/IO89RSB2
J10	TDO
J11	GDA1/IO88PDB1
J12	GDB1/IO87PDB1

FG144	
Pin Number	A3P600 Function
K1	GEB0/IO145NDB3
K2	GEA1/IO144PDB3
K3	GEA0/IO144NDB3
K4	GEA2/IO143RSB2
K5	IO119RSB2
K6	IO111RSB2
K7	GND
K8	IO94RSB2
K9	GDC2/IO91RSB2
K10	GND
K11	GDA0/IO88NDB1
K12	GDB0/IO87NDB1
L1	GND
L2	VMV3
L3	GEB2/IO142RSB2
L4	IO136RSB2
L5	VCCIB2
L6	IO115RSB2
L7	IO103RSB2
L8	IO97RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO141RSB2
M3	IO138RSB2
M4	IO123RSB2
M5	IO126RSB2
M6	IO134RSB2
M7	IO108RSB2
M8	IO99RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	A3P250 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAA1/IO01RSB0
A4	GAB0/IO02RSB0
A5	IO07RSB0
A6	IO10RSB0
A7	IO11RSB0
A8	IO15RSB0
A9	IO20RSB0
A10	IO25RSB0
A11	IO29RSB0
A12	IO33RSB0
A13	GBB1/IO38RSB0
A14	GBA0/IO39RSB0
A15	GBA1/IO40RSB0
A16	GND
B1	GAB2/IO117UDB3
B2	GAA2/IO118UDB3
B3	NC
B4	GAB1/IO03RSB0
B5	IO06RSB0
B6	IO09RSB0
B7	IO12RSB0
B8	IO16RSB0
B9	IO21RSB0
B10	IO26RSB0
B11	IO30RSB0
B12	GBC1/IO36RSB0
B13	GBB0/IO37RSB0
B14	NC
B15	GBA2/IO41PDB1
B16	IO41NDB1
C1	IO117VDB3
C2	IO118VDB3
C3	NC
C4	NC

FG256	
Pin Number	A3P250 Function
C5	GAC0/IO04RSB0
C6	GAC1/IO05RSB0
C7	IO13RSB0
C8	IO17RSB0
C9	IO22RSB0
C10	IO27RSB0
C11	IO31RSB0
C12	GBC0/IO35RSB0
C13	IO34RSB0
C14	NC
C15	IO42NPB1
C16	IO44PDB1
D1	IO114VDB3
D2	IO114UDB3
D3	GAC2/IO116UDB3
D4	NC
D5	GNDQ
D6	IO08RSB0
D7	IO14RSB0
D8	IO18RSB0
D9	IO23RSB0
D10	IO28RSB0
D11	IO32RSB0
D12	GNDQ
D13	NC
D14	GBB2/IO42PPB1
D15	NC
D16	IO44NDB1
E1	IO113PDB3
E2	NC
E3	IO116VDB3
E4	IO115UDB3
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO19RSB0

FG256	
Pin Number	A3P250 Function
E9	IO24RSB0
E10	VCCIB0
E11	VCCIB0
E12	VMV1
E13	GBC2/IO43PDB1
E14	IO46RSB1
E15	NC
E16	IO45PDB1
F1	IO113NDB3
F2	IO112PPB3
F3	NC
F4	IO115VDB3
F5	VCCIB3
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB1
F13	IO43NDB1
F14	NC
F15	IO47PPB1
F16	IO45NDB1
G1	IO111NDB3
G2	IO111PDB3
G3	IO112NPB3
G4	GFC1/IO110PPB3
G5	VCCIB3
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB1